

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Jung-Sook GOO et al.

Title:

STRAINED SILICON MOSFET HAVING IMPROVED THERMAL CONDUCTIVITY AND METHOD

FOR ITS FABRICATION

Application No.: 10/658,479

Filing Date:

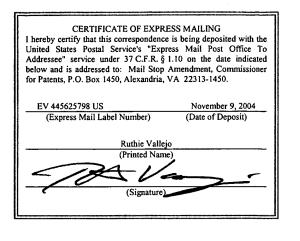
9 September 2003

Examiner:

H. TRINH

Art Unit:

2814



REPLY TO OFFICIAL ACTION OF 25 AUGUST 2004 UNDER 37 CFR §1.111

Mail Stop AMENDMENT Commissioner for Patents PO Box 1450 Alexandria, VA 22313-1450

Sir:

Applicant hereby replies to the official action mailed 25 August 2004.

Reconsideration in view of the following amendments and remarks is requested.